

isc N-Channel MOSFET Transistor

TK20J50D

DESCRIPTION

- Drain Current $I_D = 20A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 500V(\text{Min})$
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

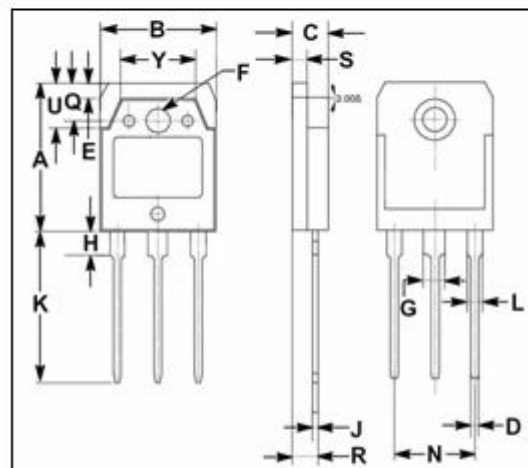
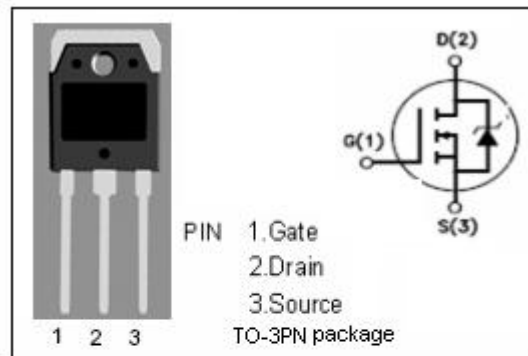
- Switching voltage regulators

ABSOLUTE MAXIMUM RATINGS($T_C = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	500	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $T_C = 25^\circ C$	20	A
$I_{D(puls)}$	Pulse Drain Current	80	A
P_{tot}	Total Dissipation@ $T_C = 25^\circ C$	280	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.45	$^\circ C/W$



DIM	mm	
	MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

isc N-Channel MOSFET Transistor**TK20J50D**• ELECTRICAL CHARACTERISTICS (T_c=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D =10mA	500			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = 10V; I _D =1mA	2.0		4.0	V
V _{SD}	Diode Forward On-Voltage	I _S =20A; V _{GS} = 0			1.7	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =10A			0.27	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±30V; V _{DS} = 0			±1	μA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V; V _{GS} = 0			10	μA